

## ABSTRACT

A silicon controlled rectifier is provided, including: a first conducting-type substrate; two second conducting-type deep wells separately disposed inside the first conducting-type substrate; a gate above the first conducting-type substrate and between the two second conducting-type deep wells; a first source/drain inside one of the two second conducting-type deep wells and at one side of the gate; a second source/drain inside the other of the two second conducting-type deep wells and at the other side of the gate; a first conducting-type doped region inside the first conducting-type substrate; and a first conducting-type doped floating region inside the one of the two second conducting-type deep wells and adjacent to the first source/drain. The first conducting-type doped floating region and the first source/drain constitute an equivalent Zener diode so that the modified silicon controlled rectifier can have a higher holding voltage.